Nan Fang

List of Publications by Year
in descending order

11	415	1040056 9	1281871 11
papers	citations	h-index	g-index

11	11	11	693
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Quantization of Mode Shifts in Nanocavities Integrated with Atomically Thin Sheets. Advanced Optical Materials, 2022, 10, .	7.3	2
2	Deterministic transfer of optical-quality carbon nanotubes for atomically defined technology. Nature Communications, 2021, 12, 3138.	12.8	16
3	Quantum-mechanical effect in atomically thin MoS 2 FET. 2D Materials, 2020, 7, 014001.	4.4	6
4	Hexagonal Boron Nitride As an Ideal Substrate for Carbon Nanotube Photonics. ACS Photonics, 2020, 7, 1773-1779.	6.6	22
5	Full Energy Spectra of Interface State Densities for nâ€•and pâ€type MoS₂ Fieldâ€Effect Transistors. Advanced Functional Materials, 2019, 29, 1904465.	14.9	39
6	Uniform and ultrathin high-Îº gate dielectrics for two-dimensional electronic devices. Nature Electronics, 2019, 2, 563-571.	26.0	204
7	Band tail interface states and quantum capacitance in a monolayer molybdenum disulfide field-effect-transistor. Journal Physics D: Applied Physics, 2018, 51, 065110.	2.8	30
8	Direct observation of electron capture and emission processes by the time domain charge pumping measurement of MoS2 FET. Applied Physics Letters, 2018, 113, .	3.3	11
9	Accumulation-Mode Two-Dimensional Field-Effect Transistor: Operation Mechanism and Thickness Scaling Rule. ACS Applied Materials & Interfaces, 2018, 10, 32355-32364.	8.0	28
10	2D Tunnel Field Effect Transistors (FETs) with a Stable Chargeâ€Transferâ€Type p⁺â€WSe₂ Source. Advanced Electronic Materials, 2018, 4, 1800207.	5.1	41
11	Experimental detection of active defects in few layers MoS ₂ through random telegraphic signals analysis observed in its FET characteristics. 2D Materials, 2017, 4, 015035.	4.4	16